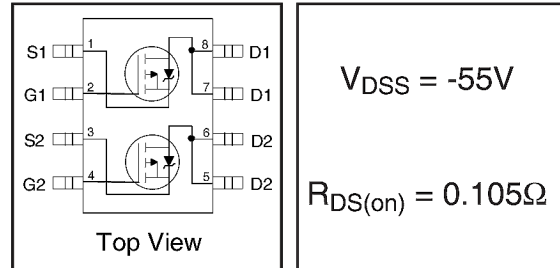


IRF7342PbF

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- Dual P-Channel Mosfet
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

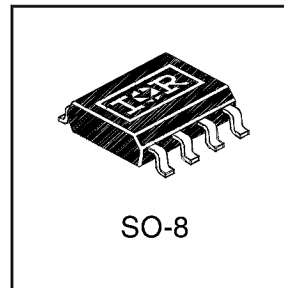


$V_{DSS} = -55V$
 $R_{DS(on)} = 0.105\Omega$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-55	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-3.4	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-2.7	
I_{DM}	Pulsed Drain Current ①	-27	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse $t_p < 10\mu s$	30	V
E_{AS}	Single Pulse Avalanche Energy ②	114	
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

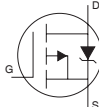
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ⑤	—	62.5	$^\circ C/W$

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.054	—	V/°C	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.095	0.105	Ω	$V_{GS} = -10V, I_D = -3.4A$ ④
		—	0.150	0.170		$V_{GS} = -4.5V, I_D = -2.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	3.3	—	—	S	$V_{DS} = -10V, I_D = -3.1A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-2.0	μA	$V_{DS} = -55V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -55V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	26	38	nC	$I_D = -3.1A$
Q_{gs}	Gate-to-Source Charge	—	3.0	4.5		$V_{DS} = -44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	8.4	13		$V_{GS} = -10V$, See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	22	ns	$V_{DD} = -28V$
t_r	Rise Time	—	10	15		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	43	64		$R_G = 6.0\Omega$
t_f	Fall Time	—	22	32		$R_D = 16\Omega$, ④
C_{iss}	Input Capacitance	—	690	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	210	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	86	—		$f = 1.0\text{MHz}$, See Fig. 9

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-27		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -2.0A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	54	80	ns	$T_J = 25^\circ\text{C}, I_F = -2.0A$
Q_{rr}	Reverse Recovery Charge	—	85	130	nC	$di/dt = -100A/\mu s$ ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting $T_J = 25^\circ\text{C}$, $L = 20\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = -3.4A$. (See Figure 8)

③ $I_{SD} \leq -3.4A$, $di/dt \leq -150A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$

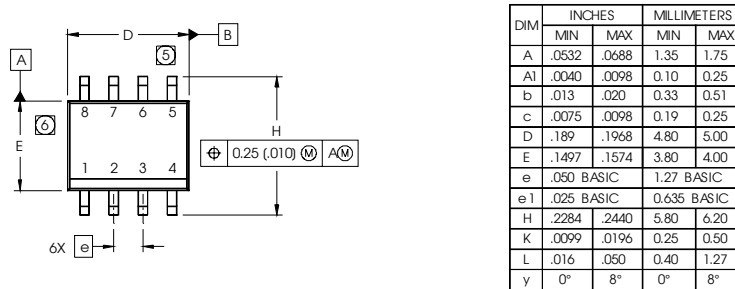
④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

⑤ When mounted on 1 inch square copper board, $t < 10$ sec

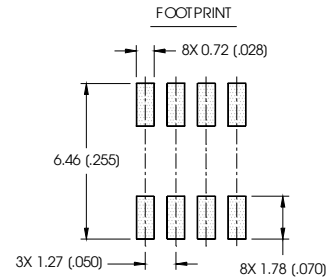
IRF7342PbF

SO-8 Package Outline

Dimensions are shown in millimeters (inches)

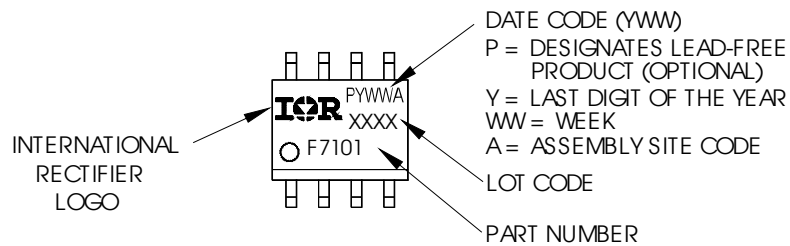


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
 5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
 6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
 7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO SUBSTRATE.



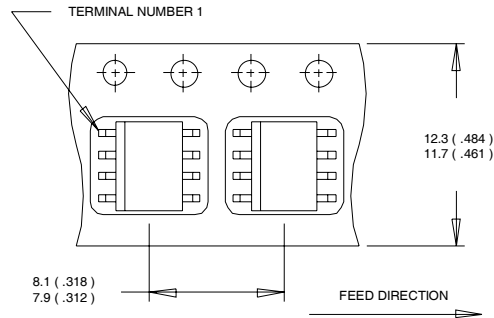
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

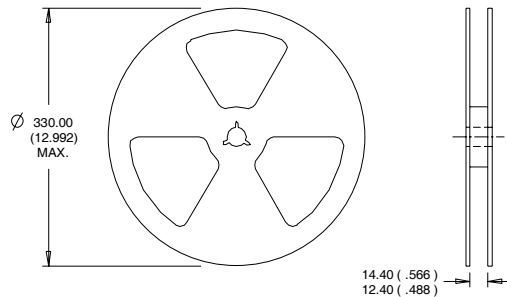


SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualifications Standards can be found on IR's Web site.